

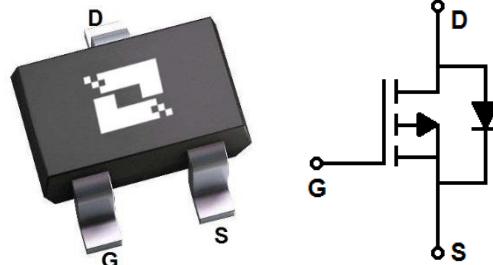
Features

- Low $R_{DS(on)}$ @ $V_{GS}=-4.5V$
- -2.5V Logic Level Control
- P Channel SOT523 Package
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ Typ}$	$I_D \text{ Max}$
-20V	125mΩ @ -4.5V	-1.5A
	142mΩ @ -3.3V	

Applications

- High-side Load Switch
- *Switching Circuits*
- *High Speed line Driver*
- *Relay Driver*

Order Information**SOT523**

Product	Package	Marking	Packing
DWZ2621	SOT523	P3	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit
Common Ratings (TA=25°C Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	±10	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 150	°C
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested①	TA=25°C	-6.0
I_D	Continuous Drain Current	TA=25°C	-1.5
		TA=70°C	-1.2
P_D	Maximum Power Dissipation	TA=25°C	0.3
		TA=70°C	0.24
$R_{θJA}$	Thermal Resistance Junction-Ambient	400	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=-250\mu\text{A}$	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current($T_A=25^\circ\text{C}$)	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	-1	μA
	Zero Gate Voltage Drain Current($T_A=125^\circ\text{C}$)	$V_{\text{DS}}=-16\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	-100	nA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 10\text{V}$, $V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=-250\mu\text{A}$	-0.35	-0.6	-1.0	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-4.5\text{V}$, $I_D=-0.75\text{A}$	-	125	200	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-3.3\text{V}$, $I_D=-0.5\text{A}$	-	142	230	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance②	$V_{\text{GS}}=-2.5\text{V}$, $I_D=-0.3\text{A}$	-	170	250	$\text{m}\Omega$
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-10\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	-	216	-	pF
C_{oss}	Output Capacitance		-	29	-	pF
C_{rss}	Reverse Transfer Capacitance		-	21	-	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=-10\text{V}$, $I_D=-0.5\text{A}$, $V_{\text{GS}}=-4.5\text{V}$	-	2.2	-	nC
Q_{gs}	Gate Source Charge		-	0.6	-	nC
Q_{gd}	Gate Drain Charge		-	0.5	-	nC
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn on Delay Time	$V_{\text{DD}}=-10\text{V}$, $I_D=-0.5\text{A}$, $R_G=3.3\Omega$, $V_{\text{GS}}=-4.5\text{V}$	-	16	-	ns
t_r	Turn on Rise Time		-	32	-	ns
$t_{\text{d}(\text{off})}$	Turn Off Delay Time		-	85	-	ns
t_f	Turn Off Fall Time		-	68	-	ns
Source Drain Diode Characteristics						
V_{SD}	Forward on voltage②	$T_J=25^\circ\text{C}$, $I_{\text{SD}}=-0.3\text{A}$, $V_{\text{GS}}=0\text{V}$	-	-0.82	-1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature

②Pulse test ; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Characteristics

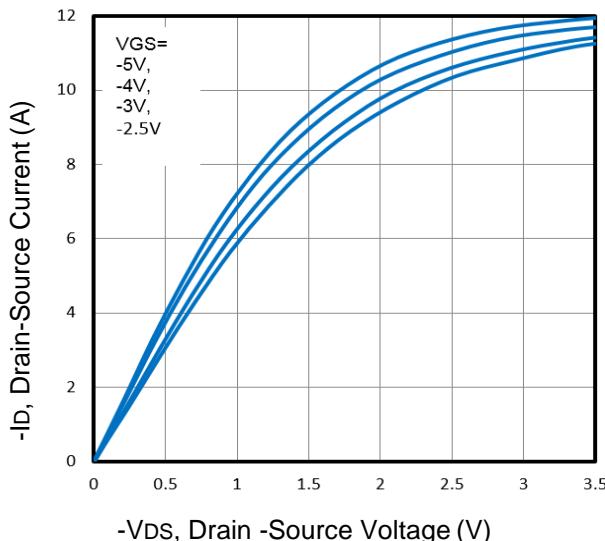


Fig1. Typical Output Characteristics

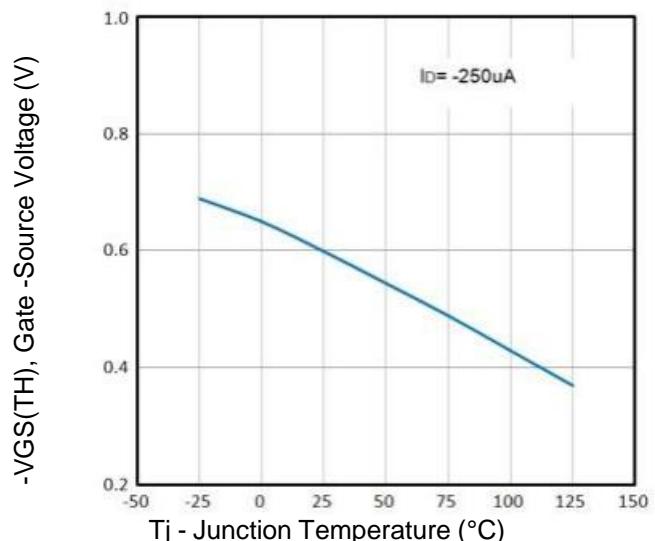


Fig2. Normalized Threshold Voltage Vs. Temperature

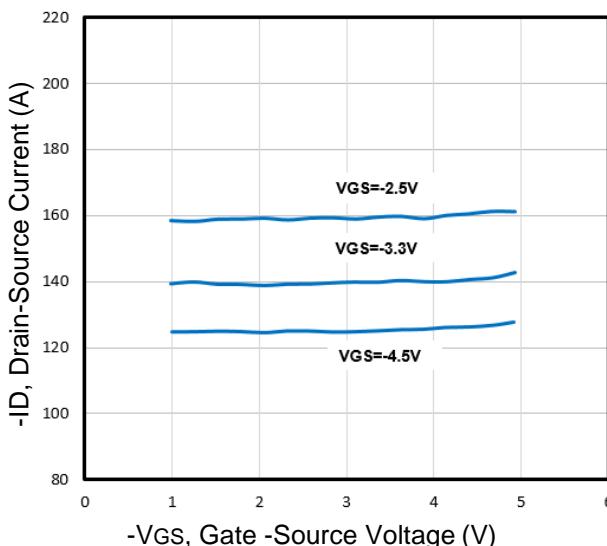


Fig3. Typical Transfer Characteristics

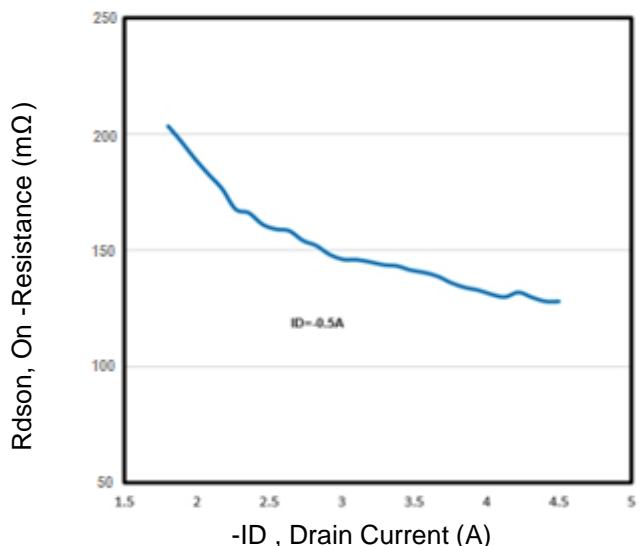


Fig4. On-Resistance vs. Drain Current and Gate

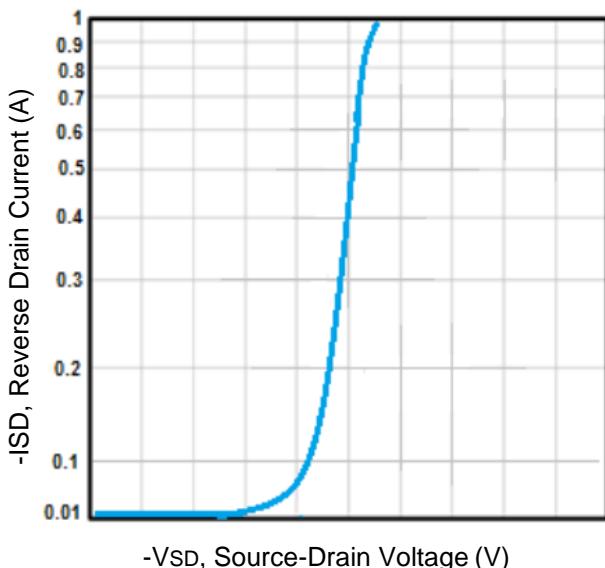


Fig5. Typical Source-Drain Diode Forward Voltage

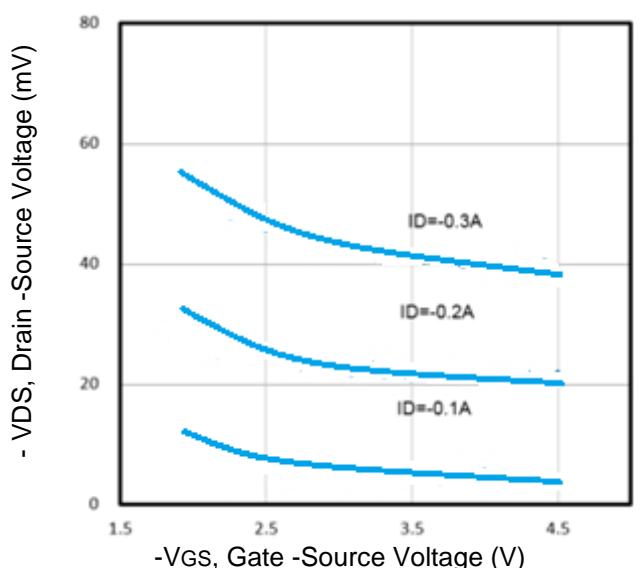


Fig6. Drain-Source Voltage vs Gate-Source Voltage

Typical Characteristics

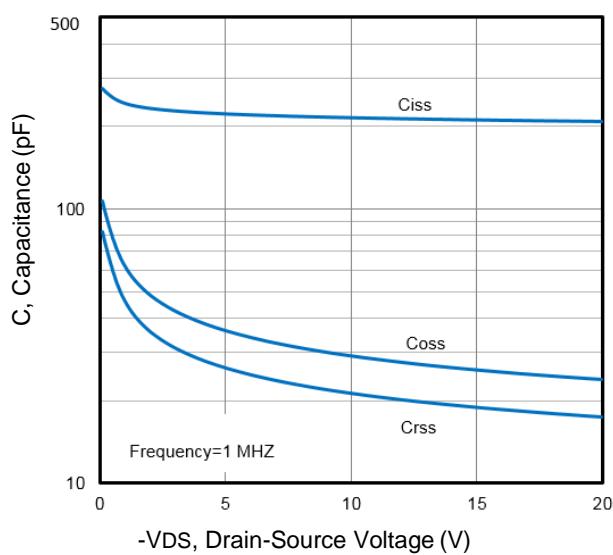


Fig7. Typical Capacitance Vs. Drain-Source Voltage

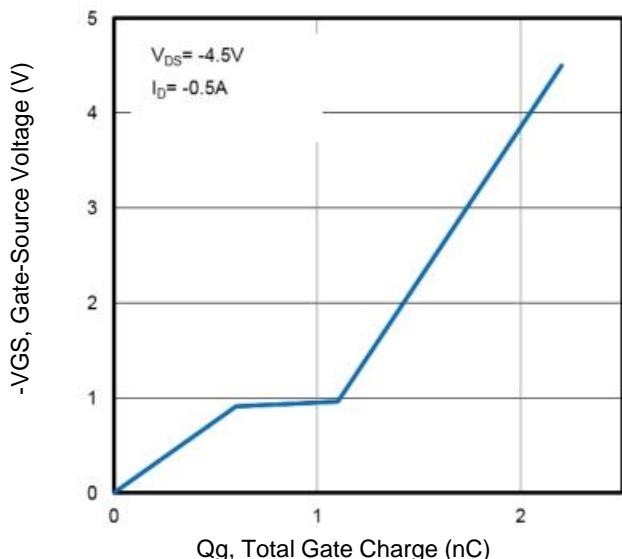
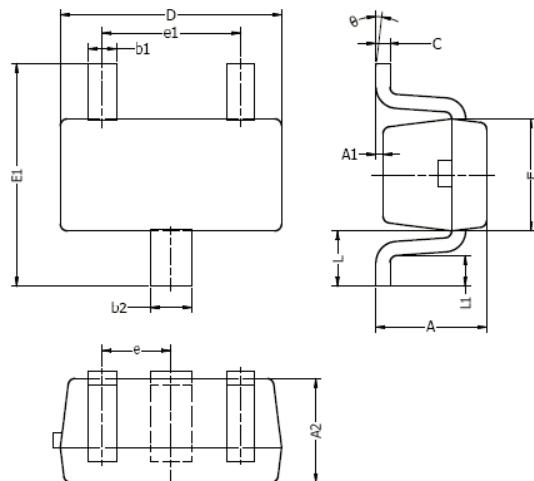
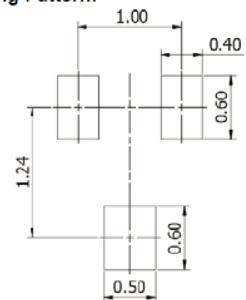


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

SOT523 Mechanical Data

Typical Soldering Pattern:


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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